

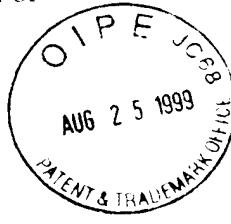
IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re PATENT APPLICATION of

UEMURA et al.

Appln. No. 08/866,129

Filed: May 30, 1997



Group Art Unit: 2814

Examiner: D. Wille

Title: METHODS AND DEVICES RELATED TO
ELECTRODE PADS FOR P-TYPE GROUP III
NITRIDE COMPOUND SEMICONDUCTORS

* * * * *

August 25, 1999

AMENDMENT/RESPONSE

Hon. Commissioner of Patents
and Trademarks
Washington, DC 20231

Sir:

In response to the Office Action dated March 25, 1999, please enter the following amendments and consider the following remarks.

Appendix I and an Information Disclosure Statement (IDS) are enclosed.

IN THE CLAIMS:

Please cancel claim 3 without prejudice or disclaimer.

Please amend the claims as follows:

1. (Amended) An electrode pad for a Group III nitride compound semiconductor having p-type conduction, comprising:
 - a first metal layer formed on [at least one of said semiconductor and] an electrode layer formed on said semiconductor, a second metal layer formed on said first metal layer, and a third metal layer formed on said second metal layer;
 - a protect film covering over said third metal layer and exposing central portion of said third metal layer;

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AUG 30 1999